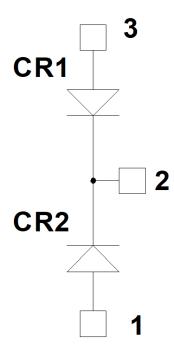
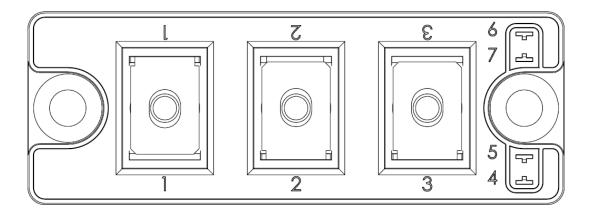


# MSCDC200KK70D1PAG Dual Common Cathode SiC Diodes Power Module

# 1 Product Overview

This section shows the product overview of the MSCDC200KK70D1PAG device.





All ratings at  $T_j$  = 25 °C, unless otherwise specified.

**Caution**: These devices are sensitive to electrostatic discharge. Proper handling procedures should be followed.



#### 1.1 Features

The following are key features of the MSCDC200A70D1PAG device:

- Silicon carbide (SiC) Schottky diode
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature-independent switching behavior
  - Positive temperature coefficient on VF
- M5 power connectors
- Aluminum nitride (AIN) substrate for improved thermal performance

#### 1.2 Benefits

The following are benefits of the MSCDC200A70D1PAG device:

- Stable temperature behavior
- Low losses
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- RoHS compliant

### 1.3 Applications

The MSCDC200A70D1PAG device is designed for the following applications:

- Welding converters
- Switched mode power supplies
- Uninterruptible power supplies



# **2** Electrical Specifications

This section shows the electrical specifications of the MSCDC200KK70D1PAG device.

#### 2.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings per SiC diode of the MSCDC200KK70D1PAG device.

**Table 1 • Absolute Maximum Ratings** 

Symbol	Parameter	Maximum Ratings	Unit	
V <sub>RRM</sub>	Repetitive peak reverse voltage		700	V
l <sub>F</sub>	DC forward current	Tc = 65 °C	200	А

The following table shows the thermal and package characteristics of the MSCDC200KK70D1PAG device.

**Table 2 • Thermal and Package Characteristics** 

Symbol	Characteristic			Min	Max	Unit
VISOL	RMS isolation voltage, any terminal to case t =1 minute, 50 Hz/60 Hz			4000		٧
Tı	Operating junction temperature range			-40	175	°C
Тлор	Recommended junction temperature under switching conditions			-40	T <sub>Jmax</sub> -25	<del></del>
Тѕтб	Storage temperature range			-40	125	_
Тс	Operating case temperature			-40	125	_
Torque	Mounting torque	For terminals	M5	2	3.5	_
		To heatsink	M6	3	5	N.m
Wt	Package weight				160	g

#### 2.2 Electrical Performance

The following table shows the electrical characteristics per SiC diode of the MSCDC200KK70D1PAG device.

**Table 3 • Electrical Characteristics** 

Symbol	Characteristic	Test Conditions	·	Min	Тур	Max	Unit
VF	Diode forward voltage	I <sub>F</sub> = 200 A	T <sub>j</sub> = 25 °C		1.5	1.8	V
			T <sub>j</sub> = 175 °C		1.9		-
Irм	Reverse leakage current	V <sub>R</sub> = 700 V	T <sub>j</sub> = 25 °C		60	800	μΑ
			T <sub>j</sub> = 175 °C		1000		=
<b>Q</b> c	Total capacitive charge	V <sub>R</sub> = 400 V			532		nC
С	Total capacitance	f = 1 MHz, V <sub>R</sub> = 200 V			992		pF
		f = 1 MHz, V <sub>R</sub> =	400 V		864		=
RthJC	Junction-to-case thermal resistance					0.241	°C/W



# 2.3 Typical Performance Curves

This section shows the typical performance curves of the MSCDC200KK70D1PAG device.

Figure 1 • Maximum Transient Thermal Impedance

#### Maximum thermal impedance

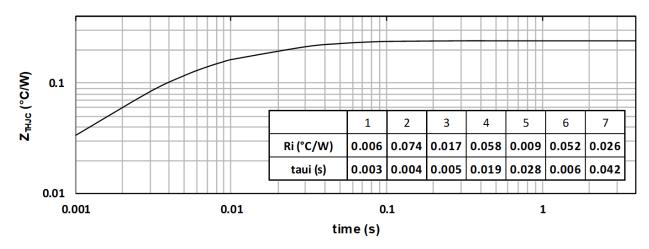


Figure 2 • Forward Current vs. Forward Voltage

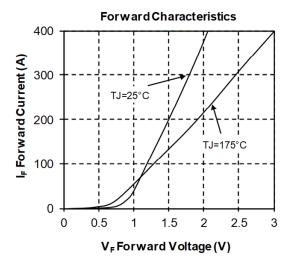
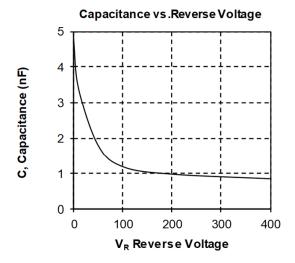


Figure 3 • Capacitance vs. Reverse Voltage





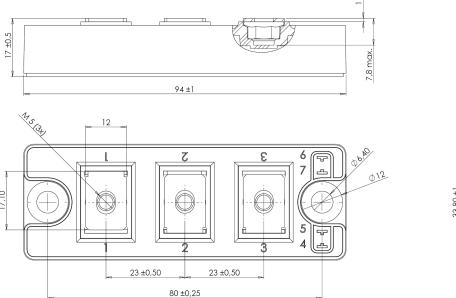
#### **Package Specification** 3

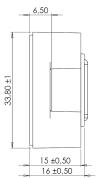
This section shows the package specifications for the MSCDC200KK70D1PAG device.

# 3.1

Package Outline Drawing
The package outline of the MSCDC200KK70D1PAG device is illustrated in this section. The dimensions in the following figure are in millimeters.

Figure 4 • Package Outline Drawing









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